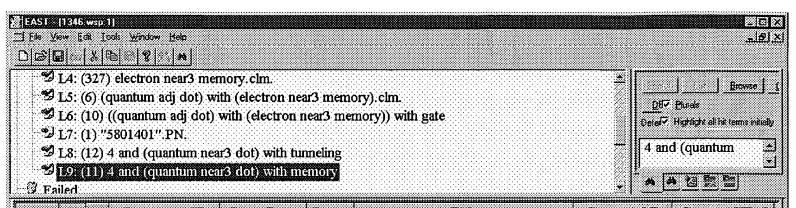


	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRe
	Г	-	US 20040076032	20040422	18	Single electron memory device	365/145	
		100	A1			comprising quantum dots between ga		
	-	,	US 20030197168	20031023	12		257/10	
			A1			layer		
	_	_	US 20030153151	20030814	12	Memory device with quantum dot	438/257	257/316;
			A 1			and method for manufacturing the sa		257/E21.209;
	_	_	US 20030054624	20030320	12	Quantum dot of single electron	438/590	257/24;
			A1			memory device and method for fabric		257/E21.345;
	_	г	US 20020167002	20021114	18	Single electron memory device	257/20	257/E21.209;
			A1			comprising quantum dots between ga		257/E29.301
	-	۳	US 20020031649	20020314	12	Quantum dot of single electron	428/209	257/E21.345;
			A1			memory device and method for fabric		257/E29.301
		_	US 6670670 B2	20031230	16	Single electron memory device	257/316	257/321;
						comprising quantum dots between ga	والموافق المرافع والموافر والموافر والموافر والموافر والموافر والمرافرة والمرافز والمرافز والمرافز	2 <i>57/</i> 325;
	-	-	US 6649966 B2	20031118	11	Quantum dot of single electron	257/314	257/315;
						memory device and method for fabric		257/316;
	l r	т-	US 6597036 B1	20030722	11	Multi-value single electron memory	257/316	257/315;
						using double-quantum dot and drivin	· · · · · · · · · · · · · · · · · · ·	257/317;
0	l r	,	US 6524883 B2	20030225	12		438/94	257/E21.345;
						memory device and method for fabric		257/E29.301;
1	l r-	_	US 6323504 B1	20011127	15	Single-electron memory device using	257/14	257/20;
		روندرونونون روندرونونون				an electron-hole coulomb blockade		257/23;
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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
)	,-	US 20040076032	20040422	18	Single electron memory device	365/145	
			A1			comprising quantum dots between ga		
	_	,	US 20030153151	20030814	12	Memory device with quantum dot	438/257	257/316;
			A 1			and method for manufacturing the sa		257/E21.209;
	-	, —	US 20030054624	20030320	12	Quantum dot of single electron	438/590	257/24;
	1		A1			memory device and method for fabric		257/E21.345;
		-	US 20020167002	20021114	18	Single electron memory device	257/20	257/E21.209;
			A 1			comprising quantum dots between ga		257/E29.301
		-	US 20020031649	20020314	12	Quantum dot of single electron	428/209	257/E21.345;
	1	1.4.7	A1			memory device and method for fabric		257/E29.301
			US 6670670 B2	20031230	16		257/316	257/321;
	1.	1.3. 1.3.				comprising quantum dots between ga		257/325;
			US 6649966 B2	20031118	11		257/314	257/315;
						memory device and method for fabric		257/316;
		-	US 6597036 B1	20030722	11	Multi-value single electron memory	257 <i>/</i> 316	257/315;
		1				using double-quantum dot and drivin		257/317;
	-		US 6524883 B2	20030225	12	Quantum dot of single electron	438/94	257/E21.345;
	1	1				memory device and method for fabric		257/E29.301;
	-	-	US 6323504 B1	20011127	15	Single-electron memory device using		257/20;
	1	1-31-1-1 1-1-1-1				an electron-hole coulomb blockade		257/23;
	_		US 5663571 A	19970902	50		257/17	257/21;
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